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orbitals, 10 so their energies are distributed over a narrow bandwidth. Similarly the short (<2.9 Å) Mn-Mn separation along c_h means the t_0 orbitals are collective, band orbitals.¹¹ The larger (≈3.7 Å) Mn-Mn separations within basal planes, on the other hand, are compatible with t_{\pm} orbitals that are either localized or, if collective, very narrow-band. These are shown as localized orbitals in Fig. 4, as narrow-band orbitals in Fig. 5.

The fact that low-temperature MnAs has a saturation moment of $\mu_0 = 3.1 \mu_B^3$ indicates that the partially filled t_{\pm} orbitals are either localized or sufficiently narrow-band to support a spontaneous magnetization of the bonding as well as the antibonding orbitals.12 This spontaneous magnetization creates an intraatomic-exchange interaction with the other d-band electrons so as to lift the spin degeneracy of all the d orbitals. We shall define ϵ_{ex} as the intra-atomic-exchange splitting of the bottom of the d bands and ϵ_{of} as the crystal-field splitting from the bottom of the α -spin t_0 band to the density-of-states minimum near the middle of the α -spin e_q bands. (A density-of-states minimum separates cation-sublattice bonding versus antibonding e_q orbitals, even though all e_q orbitals are antibonding with respect to the anion sublattice.)

Figures 4(a) and 5(a) correspond to $\epsilon_{ex} > \epsilon_{of}$, which gives a high-spin manganese moment $\mu_8 = 4\mu_B$. If $-\epsilon_{s} < (\epsilon_{\rm ex} - \epsilon_{\rm of}) < 0$, where $\epsilon_{s} = \epsilon_{1} + \epsilon_{2}$ is the energy shown in Fig. 4(b) or 5(b), then there are 0 < n < 1 electrons per atom in the β -spin t_0 orbitals, and the high-spin manganese atomic moment is somewhat reduced to

$$\mu_8 = (4 - 2n)\mu_B,\tag{8}$$

where n increases towards n=1 as $(\epsilon_{ex} - \epsilon_{ef})$ decreases towards $-\epsilon_s$. A $\mu_0 = 3.1 \mu_B$ would correspond to $n \approx 0.45$ in low-temperature MnAs.

Figures 4(b) and 5(b) correspond to $(\epsilon_{ex} - \epsilon_{of}) < -\epsilon_{o}$ and a low-spin atomic moment μ_{31} , where

$$1\mu_B < \mu_{31} < 2\mu_B. \tag{9}$$

The maximum spin-only moment is $2\mu_B$. The minimum moment of $1\mu_B$ corresponds to a spontaneous magnetization of only antibonding t_{20} electrons.

From these considerations, it follows that the condition for a $d\mu/dV > 0$ is

$$-\epsilon_{s} < (\epsilon_{\text{ex}} - \epsilon_{\text{of}}) \le 0, \quad d(\epsilon_{\text{ex}} - \epsilon_{\text{of}})/dV > 0.$$
 (10)

Since a $d\mu/dV > 0$ is restricted to a critical volume interval, this requires that over this interval

$$\Delta(\epsilon_{\rm ex} - \epsilon_{\rm of}) \geq \epsilon_{\rm s},$$
 (11)

¹⁰ J. B. Goodenough, J. Appl. Phys. 37, 1415 (1966); and speech presented at Colloque International sur les Dérives Semimétaliques, University of Paris, 1965 (unpublished).

¹¹ J. B. Goodenough, Magnetism and the Chemical Bond (John Wiley & Sons, Inc., New York, 1963).

¹² C. Guillaud [thesis, University of Strasbourg, 1943 (unpublished)] reports $\mu_0 = 3.4 \ \mu_B$. This would change n of Eq. (8) to $n \approx 0.3$ but does not alter the argument that follows because for n≈0.3, but does not alter the argument that follows because for either value 0 < n < 0.5.

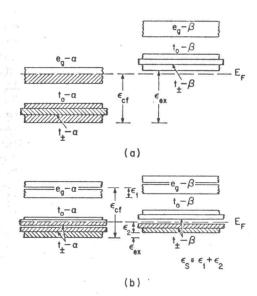


Fig. 5. Schematic one-electron energies for 3d electrons in MnAs, given collective t_{\pm} electrons: (a) high-spin manganese $(\epsilon_{\rm ex} > \epsilon_{\rm of} \text{ and } \Delta_b{}^t < \Delta_c{}^t)$ and (b) low-spin manganese $(\Delta^t{}_{ab} < \Delta_c{}^t < \Delta_b{}^t)$. Splittings of bands of low-spin phase is due to orthorhombic symmetry of B31 structures.

where an $\epsilon_s \ge 0.1$ eV can be anticipated. Now ϵ_{cf} is proportional to $V^{-1/3}$, so that

$$\Delta(-\epsilon_{\rm of}) \approx \frac{1}{3} \epsilon_{\rm of} \Delta V / V \approx 0.01 \text{ eV},$$
 (12)

where $\Delta V/V \approx 0.025$ from Eq. (3) and $\epsilon_{\rm ef} \approx 1-2$ eV is known from spectroscopic data. The fact that $\Delta(-\epsilon_{\text{of}}) < kT$ in the critical temperature interval shows that the low-spin high-spin transition cannot be due $d(-\epsilon_{\rm of})/dV$ alone, and we are forced to assume that

$$\Delta \epsilon_{\text{ex}} = \langle d\epsilon_{\text{ex}}/dV \rangle \Delta V \geq 0.1 \text{ eV}$$
 (13)

within the small, critical volume interval. This, in turn, implies that there is a critical molar volume, and hence a critical bandwidth for the t_+ electrons, at which there is a sharp change in the magnitude of the intraatomic-exchange splitting responsible for a spontaneous atomic moment.

Note that with $\mu_8 = 3.1 \mu_B$, $\mu_8^{*2} \approx 17 \mu_B^2$. Therefore Eq. (7) requires $\mu_{31}^{*2} \ge 5.3 \mu_B^2$, which from Eq. (9) is satisfied so long as μ_{31} * refers to the intermediate state of Eq. (10).

2. Origin of a Sharp Change in ϵ_{ex} with Bandwidth

Spontaneous atomic moments may occur if the d electrons are localized. Measurements13 on LaCoO3 appear to have demonstrated that, in this compound at least, a localized-electron and a collective-electron state correspond to two thermodynamically different electronic phases and that there is a first-order phase change from one to the other at some critical overlap integral A. In a tight-binding approximation, the

¹³ P. M. Raccah and J. B. Goodenough, Phys. Rev. 155, 932 (1967).